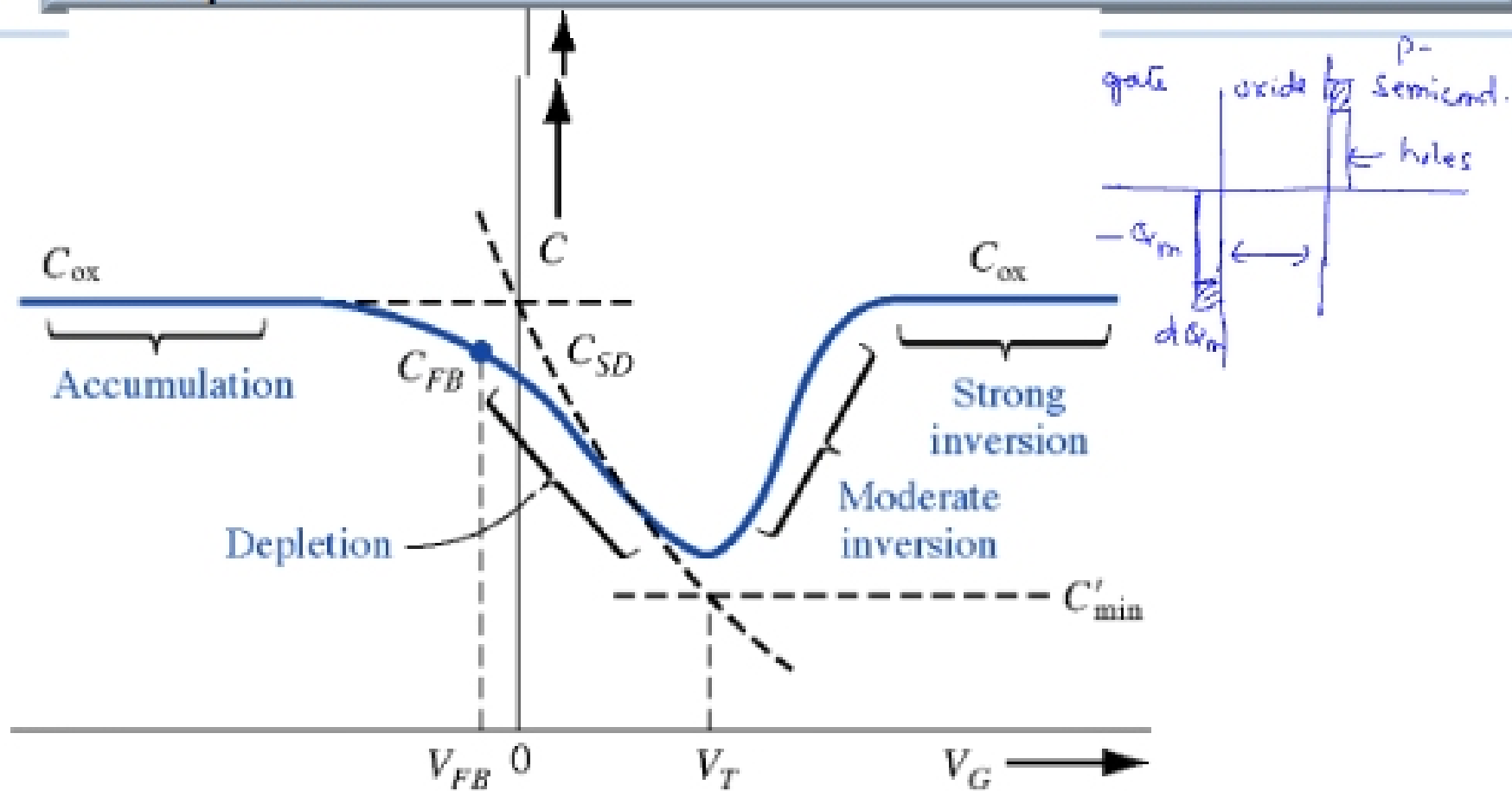




- **MOS Capacitance measurement generates a wealth of information about the oxide – semiconductor interface**
- **Frequency dependence is expected since the inversion depends on minority carrier generation which takes a “finite” time**
 - **Low Frequency: Measurement maintains equilibrium with applied gate bias at all times. You can probe the inversion charge along with the depletion and accumulation charge**
 - **High Frequency: Minority carriers needed for inversion cannot respond as fast. You can only probe only the depletion region charge**



- In accumulation: